

CM200DX-24A

HIGH POWER SWITCHING USE
INSULATED TYPE

CM200DX-24A

- 5th Generation NX series -

Collector current I_C 200 A

Collector-emitter voltage V_{CES} 1200 V

Maximum junction temperature T_{jmax} ... 150 °C



Dual (Half-Bridge)

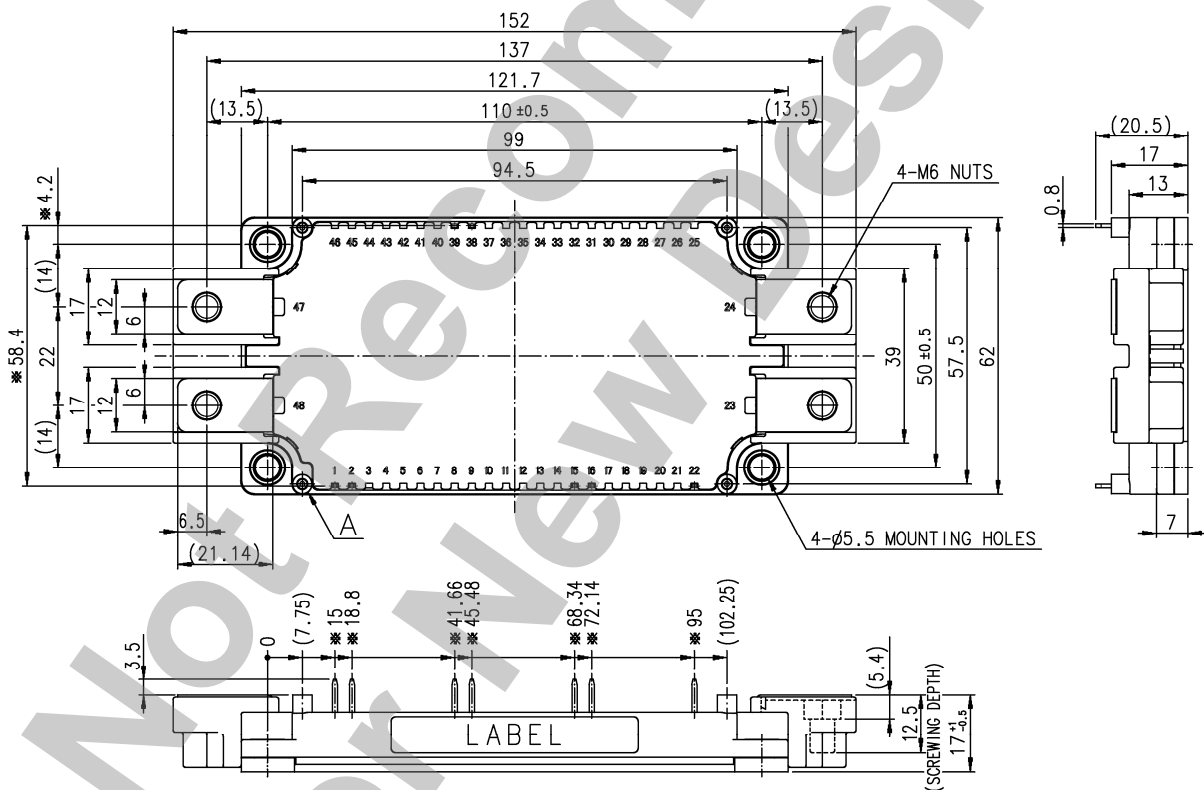
- Flat base Type
- Copper base plate (non-plating)
- RoHS Directive compliant
- UL Recognized under UL1557, File E323585

APPLICATION

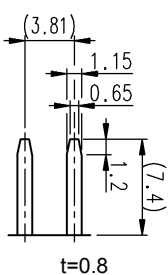
AC Motor Control, Motion/Servo Control, Power supply, etc.

OUTLINE DRAWING & INTERNAL CONNECTION

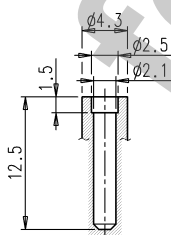
Dimension in mm



TERMINAL



SECTION A

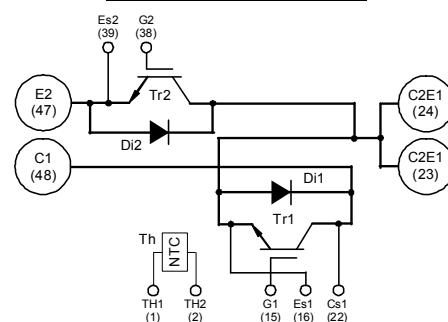


Tolerance otherwise specified

Division of Dimension	Tolerance
0.5 to 3	±0.2
over 3 to 6	±0.3
over 6 to 30	±0.5
over 30 to 120	±0.8
over 120 to 400	±1.2

※: Dimensions with a
Tolerance of $\pm \square \square \square \square$

INTERNAL CONNECTION



ABSOLUTE MAXIMUM RATINGS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWDI

Symbol	Item	Conditions	Rating	Unit
V_{CES}	Collector-emitter voltage	G-E short-circuited	1200	V
V_{GES}	Gate-emitter voltage	C-E short-circuited	± 20	V
I_C	Collector current	DC, $T_C=90\text{ }^\circ\text{C}$ (Note.2, 4)	200	A
I_{CRM}		Pulse, Repetitive (Note.3)	400	
P_{tot}	Total power dissipation	$T_C=25\text{ }^\circ\text{C}$ (Note.2, 4)	1250	W
I_E (Note.1)	Emitter current	$T_C=25\text{ }^\circ\text{C}$ (Note.2, 4)	200	A
I_{ERM} (Note.1)	(Free wheeling diode forward current)	Pulse, Repetitive (Note.3)	400	

MODULE

Symbol	Item	Conditions	Rating	Unit
T_{jmax}	Maximum junction temperature	-	150	$^\circ\text{C}$
T_{Cmax}	Maximum case temperature	(Note.2)	125	
T_{jop}	Operating junction temperature	-	-40 ~ +150	$^\circ\text{C}$
T_{stg}	Storage temperature	-	-40 ~ +125	
V_{isol}	Isolation voltage	Terminals to base plate, RMS, $f=60\text{ Hz}$, AC 1 min	2500	V

ELECTRICAL CHARACTERISTICS ($T_j=25\text{ }^\circ\text{C}$, unless otherwise specified)

INVERTER PART IGBT/FWDI

Symbol	Item	Conditions	Limits			Unit	
			Min.	Typ.	Max.		
I_{CES}	Collector-emitter cut-off current	$V_{CE}=V_{CES}$, G-E short-circuited	-	-	1	mA	
I_{GES}	Gate-emitter leakage current	$V_{GE}=V_{GES}$, C-E short-circuited	-	-	0.5	μA	
$V_{GE(th)}$	Gate-emitter threshold voltage	$I_C=20\text{ mA}$, $V_{CE}=10\text{ V}$	6	7	8	V	
V_{CESat} (Terminal)	Collector-emitter saturation voltage	$I_C=200\text{ A}$ (Note.5), $V_{GE}=15\text{ V}$	$T_j=25\text{ }^\circ\text{C}$	-	2.0	2.6	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.2	-	
V_{CESat} (Chip)	Collector-emitter saturation voltage	$I_C=200\text{ A}$, $V_{GE}=15\text{ V}$ (Note.5)	-	1.9	-	V	
C_{ies}	Input capacitance	$V_{CE}=10\text{ V}$, G-E short-circuited	-	-	35	nF	
C_{oes}	Output capacitance		-	-	3.0		
C_{res}	Reverse transfer capacitance		-	-	0.68		
Q_G	Gate charge	$V_{CC}=600\text{ V}$, $I_C=200\text{ A}$, $V_{GE}=15\text{ V}$	-	1000	-	nC	
$t_{d(on)}$	Turn-on delay time	$V_{CC}=600\text{ V}$, $I_C=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=1.6\text{ }\Omega$, Inductive load	-	-	130	ns	
t_r	Rise time		-	-	100		
$t_{d(off)}$	Turn-off delay time		-	-	450		
t_f	Fall time		-	-	600		
V_{EC} (Note.1) (Terminal)	Emitter-collector voltage	$I_E=200\text{ A}$ (Note.5), G-E short-circuited	$T_j=25\text{ }^\circ\text{C}$	-	2.6	3.4	V
			$T_j=125\text{ }^\circ\text{C}$	-	2.16	-	
V_{EC} (Note.1) (Chip)	Emitter-collector voltage	$I_E=200\text{ A}$, G-E short-circuited (Note.5)	-	2.5	-	V	
t_{rr} (Note.1)	Reverse recovery time	$V_{CC}=600\text{ V}$, $I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=1.6\text{ }\Omega$, Inductive load	-	-	150	ns	
Q_{rr} (Note.1)	Reverse recovery charge		-	9.0	-	μC	
E_{on}	Turn-on switching energy per pulse	$V_{CC}=600\text{ V}$, $I_C=I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$, $R_G=1.6\text{ }\Omega$, $T_j=125\text{ }^\circ\text{C}$,	-	8.0	-	mJ	
E_{off}	Turn-off switching energy per pulse	Inductive load	-	22.5	-		
E_{rr} (Note.1)	Reverse recovery energy per pulse		-	17	-	mJ	
$R_{CC'+EE'}$	Internal lead resistance	Main terminals-chip, per switch, $T_C=25\text{ }^\circ\text{C}$ (Note.2)	-	1.6	-	m Ω	
r_g	Internal gate resistance	Per switch, $T_C=25\text{ }^\circ\text{C}$ (Note.2)	-	0	-	Ω	

ELECTRICAL CHARACTERISTICS (cont.; T_j=25 °C, unless otherwise specified)

NTC THERMISTOR PART

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R ₂₅	Zero-power resistance	T _C =25 °C (Note.2)	4.85	5.00	5.15	kΩ
ΔR/R	Deviation of resistance	T _C =100 °C, R ₁₀₀ =493 Ω	-7.3	-	+7.8	%
B _(25/50)	B-constant	Approximate by equation (Note.6)	-	3375	-	K
P ₂₅	Power dissipation	T _C =25 °C (Note.2)	-	-	10	mW

THERMAL RESISTANCE CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
R _{th(j-c)Q}	Thermal resistance (Note.2)	Junction to case, per Inverter IGBT	-	-	0.10	K/W
R _{th(j-c)D}		Junction to case, per Inverter FWDi	-	-	0.19	K/W
R _{th(c-s)}	Contact thermal resistance (Note.2)	Case to heat sink, per 1 module, Thermal grease applied (Note.7)	-	15	-	K/kW

MECHANICAL CHARACTERISTICS

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
M _t	Mounting torque	Main terminals M 6 screw	3.5	4.0	4.5	N·m
M _s		Mounting to heat sink M 5 screw	2.5	3.0	3.5	
d _s	Creepage distance	Terminal to terminal	11.55	-	-	mm
		Terminal to base plate	12.32	-	-	
d _a	Clearance	Terminal to terminal	10.00	-	-	mm
		Terminal to base plate	10.85	-	-	
m	Weight	-	-	330	-	g
e _c	Flatness of base plate	On the centerline X, Y (Note.8)	±0	-	+100	μm

Note.1: Represent ratings and characteristics of the anti-parallel, emitter-collector free wheeling diode (FWDi).

Note.2: Case temperature (T_C) and heat sink temperature (T_S) are defined on the each surface (mounting side) of base plate and heat sink just under the chips. Refer to the figure of chip location.
The heat sink thermal resistance should measure just under the chips.

Note.3: Pulse width and repetition rate should be such that the device junction temperature (T_j) dose not exceed T_{jmax} rating.

Note.4: Junction temperature (T_j) should not increase beyond T_{jmax} rating.

Note.5: Pulse width and repetition rate should be such as to cause negligible temperature rise.
Refer to the figure of test circuit.

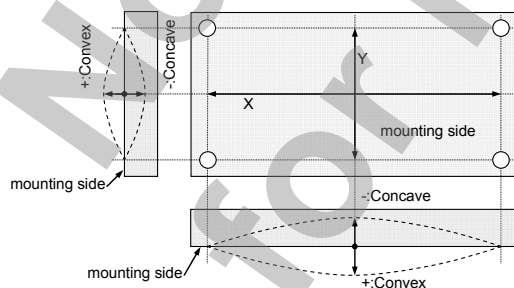
Note.6: $B_{(25/50)} = \ln\left(\frac{R_{25}}{R_{50}}\right) / \left(\frac{1}{T_{25}} - \frac{1}{T_{50}}\right)$

R₂₅: resistance at absolute temperature T₂₅ [K]; T₂₅=25 [°C]+273.15=298.15 [K]

R₅₀: resistance at absolute temperature T₅₀ [K]; T₅₀=50 [°C]+273.15=323.15 [K]

Note.7: Typical value is measured by using thermally conductive grease of λ=0.9 W/(m·K).

Note.8: Base plate (mounting side) flatness measurement points (X, Y) are as follows of the following figure.



Note.9: JAPAN Electronics and Information Technology Industries Association (JEITA) standard,

"ED-4701/300: Environmental and endurance test methods for semiconductor devices (Stress test I)".

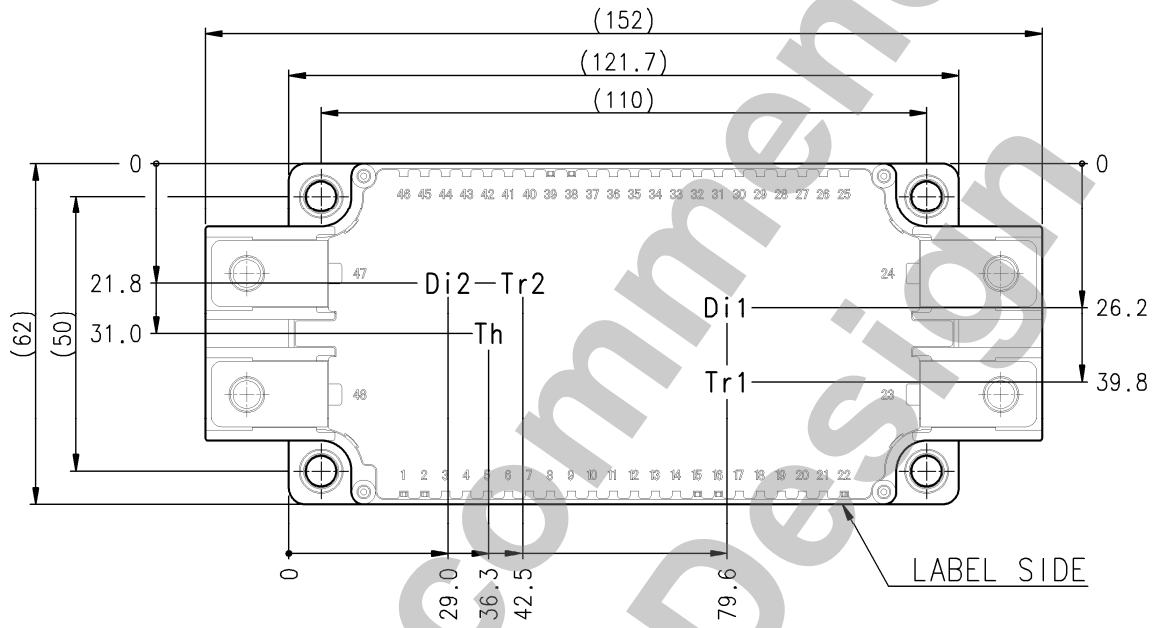
MITSUBISHI IGBT MODULES
CM200DX-24A
 HIGH POWER SWITCHING USE
 INSULATED TYPE

RECOMMENDED OPERATING CONDITIONS ($T_a=25\text{ }^\circ\text{C}$)

Symbol	Item	Conditions	Limits			Unit
			Min.	Typ.	Max.	
V_{CC}	(DC) Supply voltage	Applied across C1-E2	-	600	800	V
V_{GEon}	Gate (-emitter drive) voltage	Applied across G1-Es1/G2-Es2	13.5	15.0	16.5	V
R_G	External gate resistance	Per switch	1.6	-	16	Ω

CHIP LOCATION (Top view)

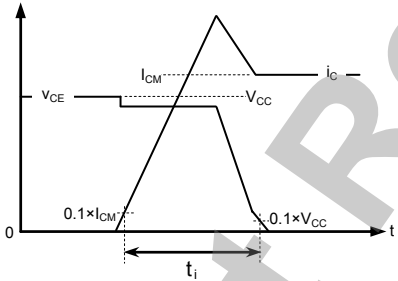
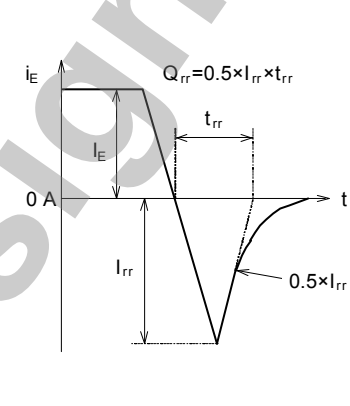
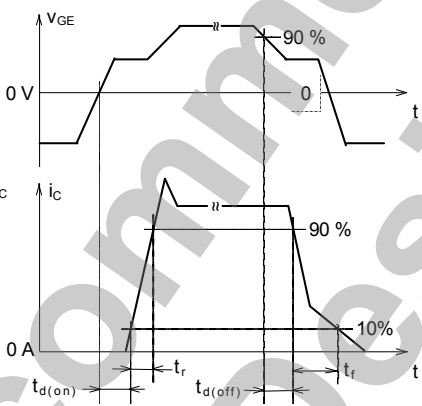
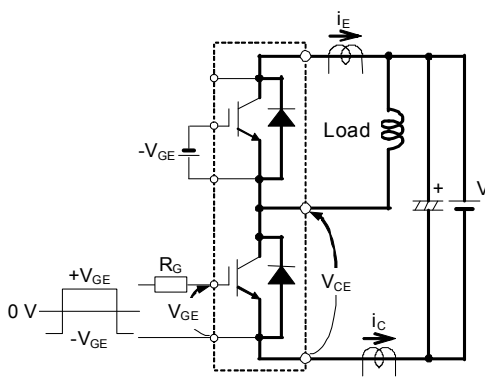
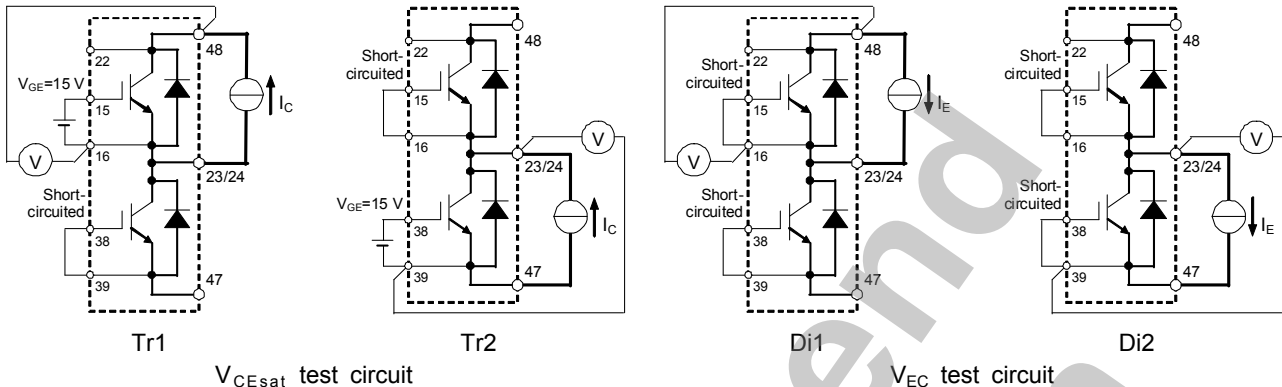
Dimension in mm, tolerance: $\pm 1\text{ mm}$



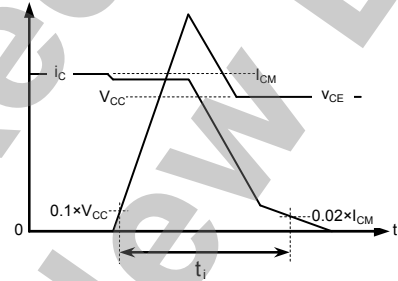
Tr1/Tr2: IGBT, Di1/Di2: FWDi, Th: NTC thermistor. Each mark points the center position of each chip.

Not Recommended for New Design

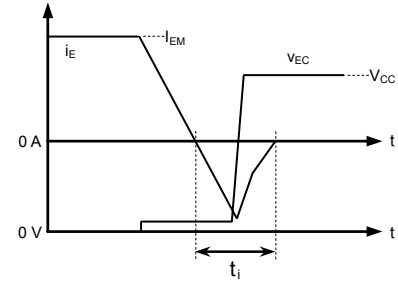
TEST CIRCUIT AND WAVEFORMS



IGBT Turn-on switching energy



IGBT Turn-off switching energy



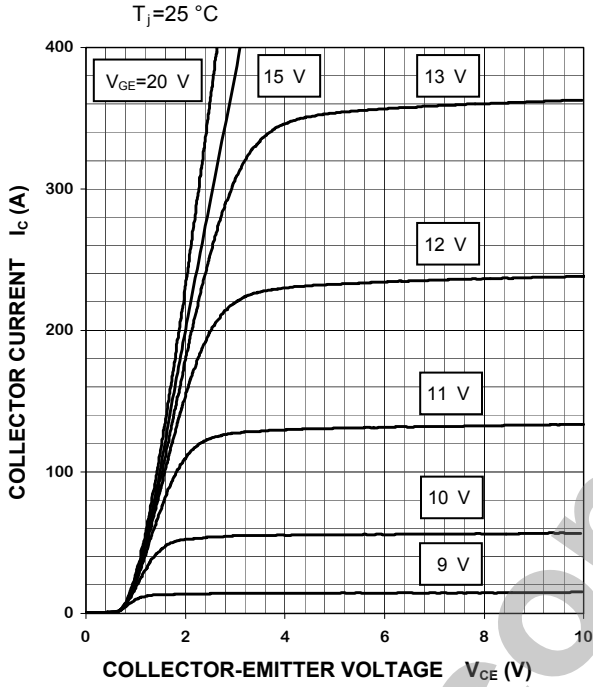
FWDi Reverse recovery energy

Turn-on / Turn-off switching energy and Reverse recovery energy test waveforms (Integral time instruction drawing)

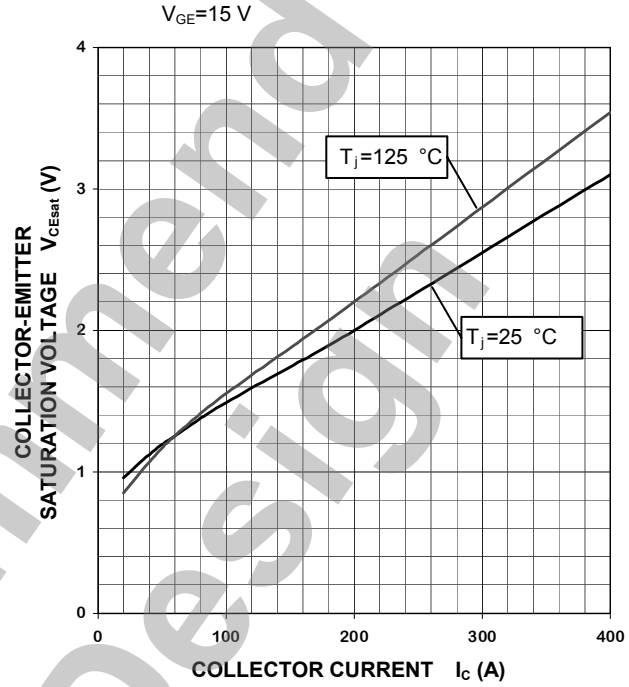
PERFORMANCE CURVES

INVERTER PART

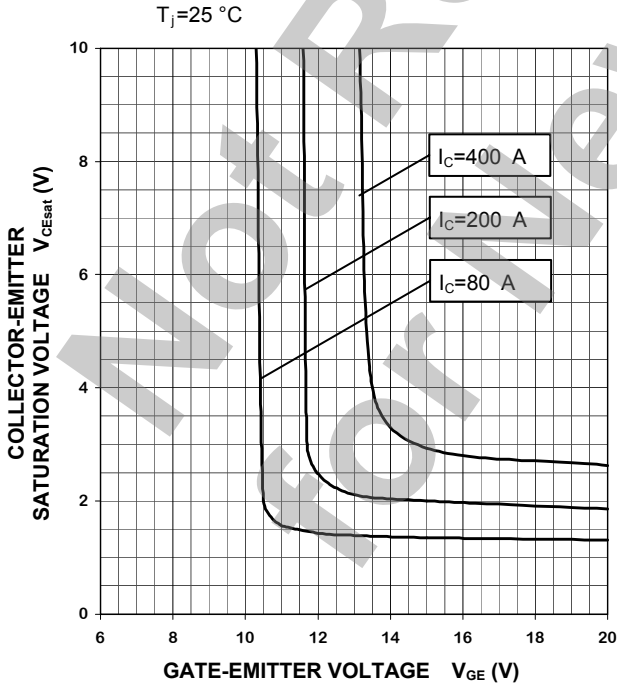
OUTPUT CHARACTERISTICS (TYPICAL)



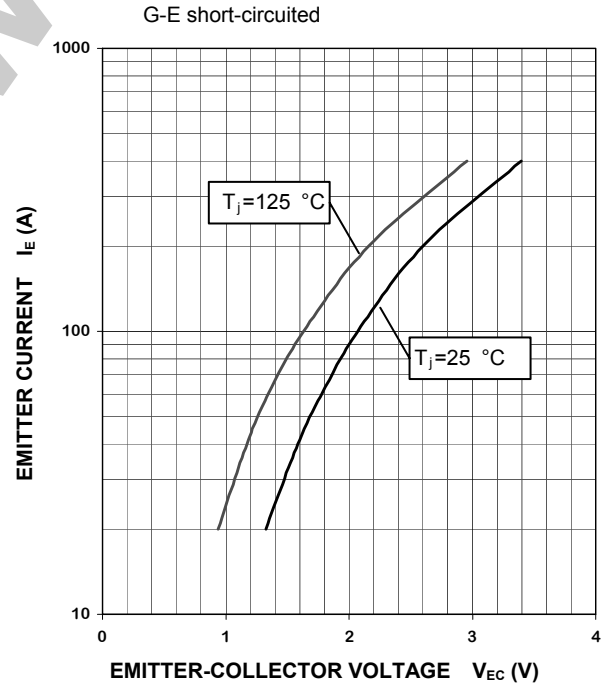
COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



COLLECTOR-EMITTER SATURATION VOLTAGE CHARACTERISTICS (TYPICAL)



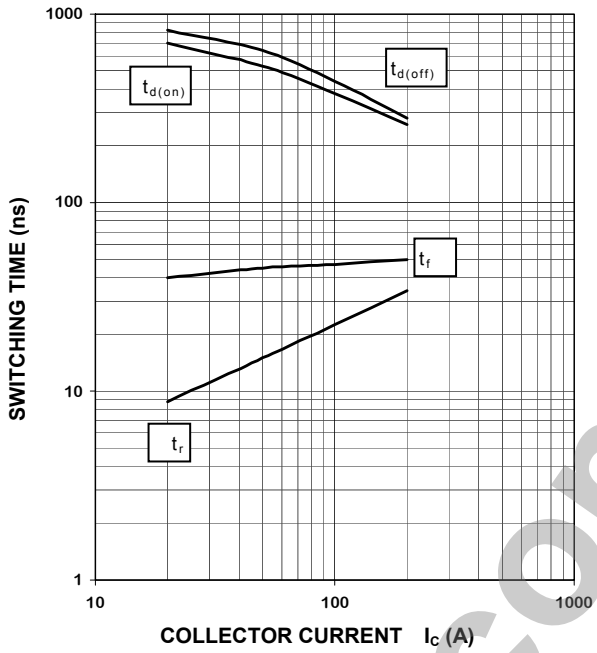
FREE WHEELING DIODE FORWARD CHARACTERISTICS (TYPICAL)



MITSUBISHI IGBT MODULES
CM200DX-24A
 HIGH POWER SWITCHING USE
 INSULATED TYPE

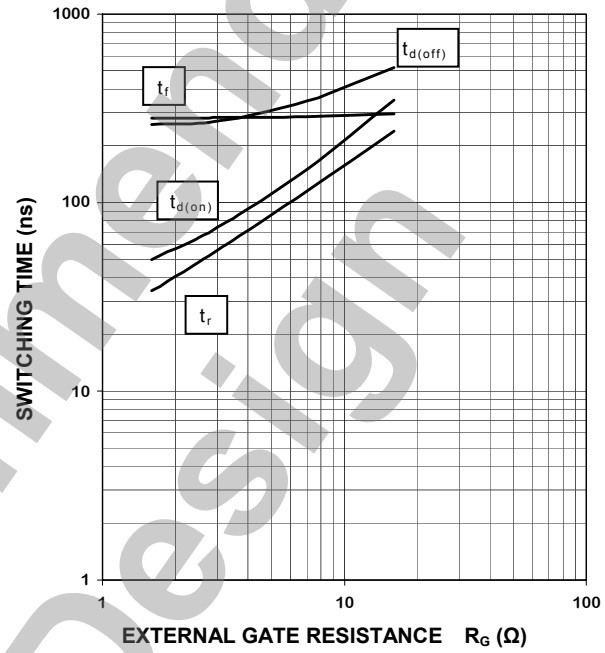
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=1.6\ \Omega$,
 INDUCTIVE LOAD, $T_j=125\text{ }^\circ\text{C}$



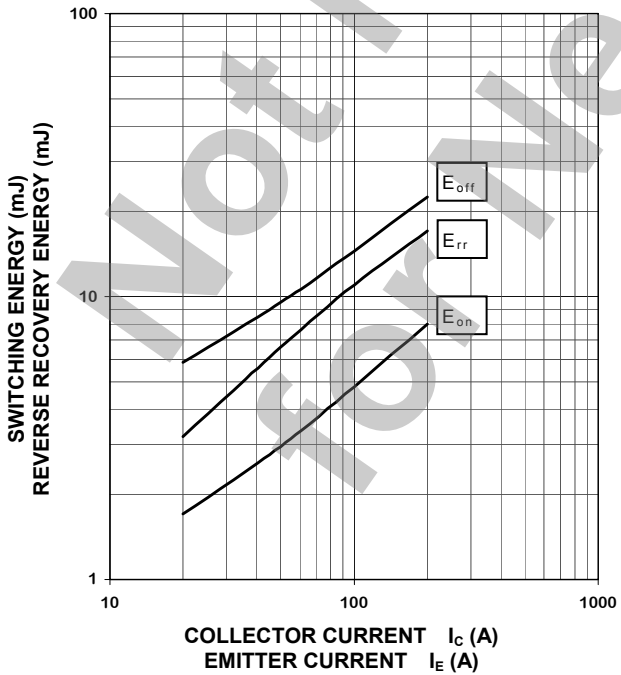
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $I_C=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
 INDUCTIVE LOAD, $T_j=125\text{ }^\circ\text{C}$



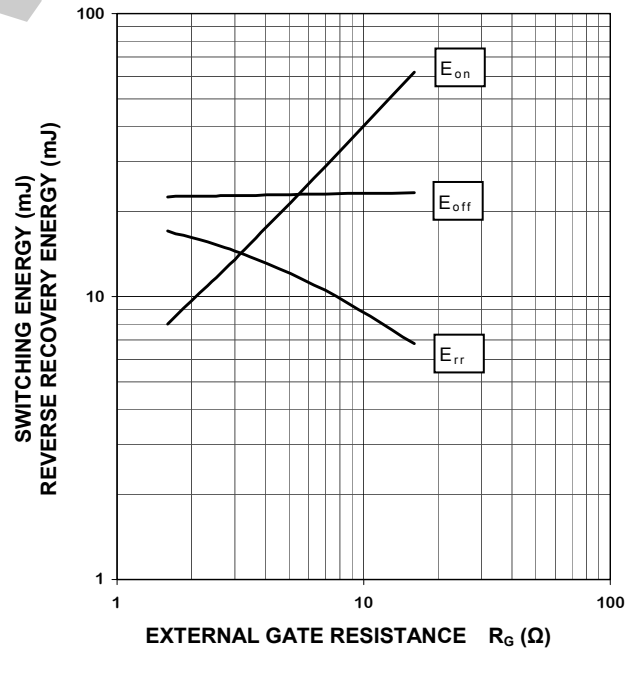
HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=1.6\ \Omega$,
 INDUCTIVE LOAD, PER PULSE, $T_j=125\text{ }^\circ\text{C}$



HALF-BRIDGE SWITCHING CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $I_C/I_E=200\text{ A}$, $V_{GE}=\pm 15\text{ V}$,
 INDUCTIVE LOAD, PER PULSE, $T_j=125\text{ }^\circ\text{C}$

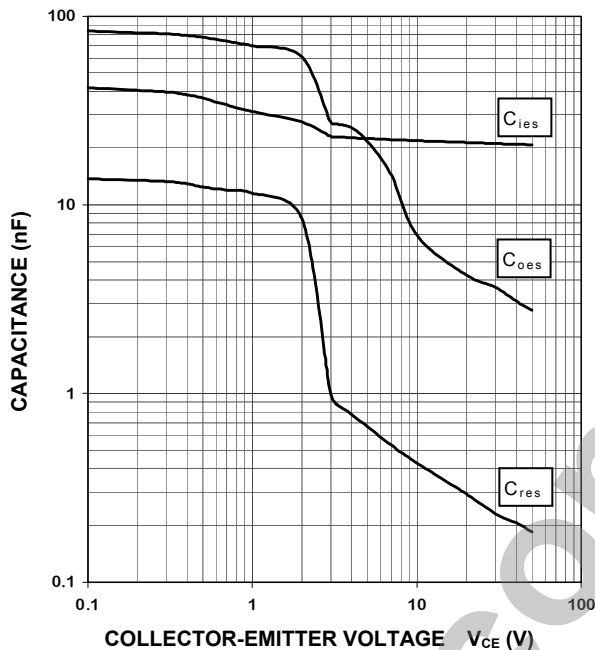


CM200DX-24A

HIGH POWER SWITCHING USE
INSULATED TYPE

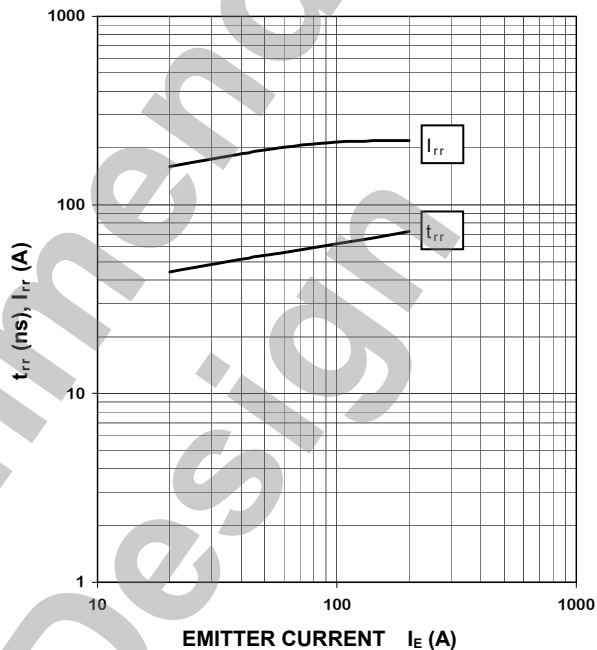
CAPACITANCE CHARACTERISTICS (TYPICAL)

G-E short-circuited, $T_J=25\text{ }^\circ\text{C}$



FREE WHEELING DIODE REVERSE RECOVERY CHARACTERISTICS (TYPICAL)

$V_{CC}=600\text{ V}$, $V_{GE}=\pm 15\text{ V}$, $R_G=1.6\ \Omega$,
INDUCTIVE LOAD, $T_J=25\text{ }^\circ\text{C}$



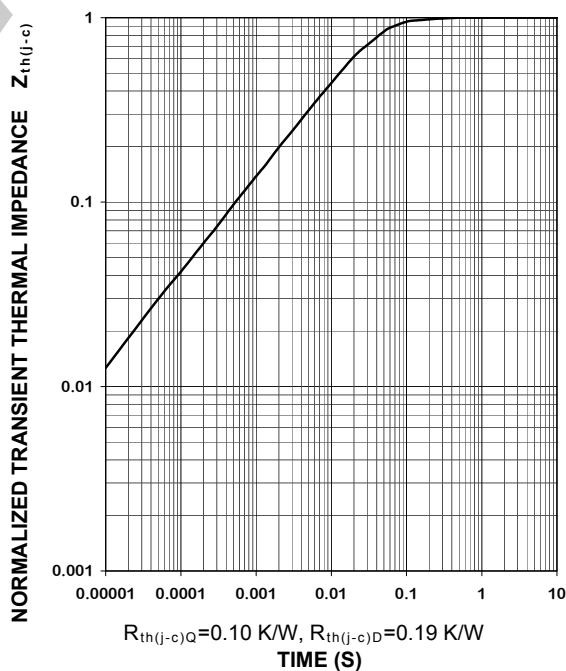
GATE CHARGE CHARACTERISTICS (TYPICAL)

$I_C=200\text{ A}$, $T_J=25\text{ }^\circ\text{C}$



TRANSIENT THERMAL IMPEDANCE CHARACTERISTICS (MAXIMUM)

Single pulse, $T_C=25\text{ }^\circ\text{C}$



Keep safety first in your circuit designs!

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